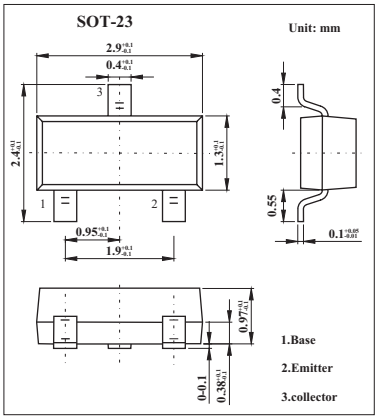
NPN Silicon Epitaxial Transistor

2SC1623



■ Features

- High DC Current Gain: h_{FE} = 200 Typ. (V_{CE} = 6.0V, I_C = 1.0mA)
- High Voltage: V_{CEO} = 50V
- Complementary to 2SA812

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	50	V
Collector-Base Voltage	V_{CBO}	60	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	100	mA
Total Power Dissipation	P_T	200	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	V_{CB} = 60V, I_E = 0			0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 5.0V , I_C = 0			0.1	μA
DC Current Gain *	h_{FE}	I_C = 1.0mA , V_{CE} = 6.0V	90	200	600	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$	I_C = 100mA , I_B = 10mA		0.15	0.3	V
Base to Saturation Voltage *	$V_{BE(sat)}$	I_C = 100mA , I_B = 10mA		0.86	1.0	V
Base to Emitter Voltage *	V_{BE}	V_{CE} = 6.0V, I_C = 1.0mA	0.55	0.62	0.65	V
Gain Bandwidth Product	f_T	V_{CE} = 6.0V , I_E = -10mA		250		MHz
Output Capacitance	C_{OB}	V_{CB} = 6.0V , I_E = 0, f = 1MHz		3.0		pF

* Pulsed: PW ≤350μs, D.C. ≤2%.

■ h_{FE} Classification

Marking	L4	L5	L6	L7
h_{FE}	90 ～ 180	135 ～ 270	200 ～ 400	300 ～ 600